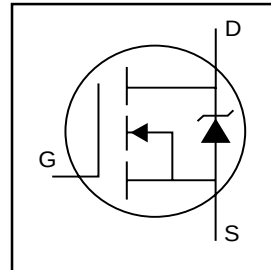


# IRFZ44VS

# IRFZ44VL

HEXFET® Power MOSFET

- Advanced Process Technology
- Ultra Low On-Resistance
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Optimized for SMPS Applications

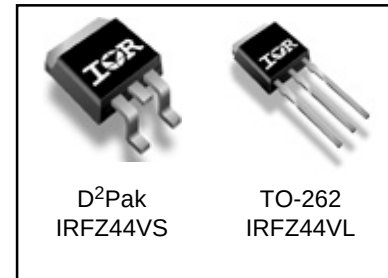


|                            |
|----------------------------|
| $V_{DS} = 60V$             |
| $R_{DS(on)} = 16.5m\Omega$ |
| $I_D = 55A$                |

## Description

Advanced HEXFET® Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The D<sup>2</sup>Pak is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D<sup>2</sup>Pak is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application. The through-hole version (IRFZ44VL) is available for low-profile applications.



D<sup>2</sup>Pak  
IRFZ44VS

TO-262  
IRFZ44VL

## Absolute Maximum Ratings

|                           | Parameter                                | Max.         | Units |
|---------------------------|------------------------------------------|--------------|-------|
| $I_D @ T_C = 25^\circ C$  | Continuous Drain Current, $V_{GS} @ 10V$ | 55           | A     |
| $I_D @ T_C = 100^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V$ | 39           |       |
| $I_{DM}$                  | Pulsed Drain Current ①                   | 220          |       |
| $P_D @ T_C = 25^\circ C$  | Power Dissipation                        | 115          | W     |
|                           | Linear Derating Factor                   | 0.77         | W/°C  |
| $V_{GS}$                  | Gate-to-Source Voltage                   | $\pm 20$     | V     |
| $E_{AS}$                  | Single Pulse Avalanche Energy②           | 115          | mJ    |
| $I_{AR}$                  | Avalanche Current①                       | 55           | A     |
| $E_{AR}$                  | Repetitive Avalanche Energy①             | 11           | mJ    |
| dv/dt                     | Peak Diode Recovery dv/dt ③              | 4.5          | V/ns  |
| $T_J$                     | Operating Junction and                   | -55 to + 175 | °C    |
| $T_{STG}$                 | Storage Temperature Range                |              |       |
|                           | Soldering Temperature, for 10 seconds    |              |       |

## Thermal Resistance

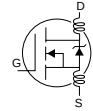
|                 | Parameter           | Typ. | Max. | Units |
|-----------------|---------------------|------|------|-------|
| $R_{\theta JC}$ | Junction-to-Case    | —    | 1.3  | °C/W  |
| $R_{\theta JA}$ | Junction-to-Ambient | —    | 40   |       |

# IRFZ44VS/IRFZ44VL

International  
**IR** Rectifier

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

|                                 | Parameter                            | Min. | Typ.  | Max. | Units | Conditions                                                                  |
|---------------------------------|--------------------------------------|------|-------|------|-------|-----------------------------------------------------------------------------|
| $V_{(BR)DSS}$                   | Drain-to-Source Breakdown Voltage    | 60   | —     | —    | V     | $V_{GS} = 0V, I_D = 250\mu A$                                               |
| $\Delta V_{(BR)DSS}/\Delta T_J$ | Breakdown Voltage Temp. Coefficient  | —    | 0.062 | —    | V/°C  | Reference to $25^\circ\text{C}$ , $I_D = 1mA$                               |
| $R_{DS(on)}$                    | Static Drain-to-Source On-Resistance | —    | —     | 16.5 | mΩ    | $V_{GS} = 10V, I_D = 31A$ ④                                                 |
| $V_{GS(th)}$                    | Gate Threshold Voltage               | 2.0  | —     | 4.0  | V     | $V_{DS} = V_{GS}, I_D = 250\mu A$                                           |
| $g_{fs}$                        | Forward Transconductance             | 24   | —     | —    | S     | $V_{DS} = 25V, I_D = 31A$ ④                                                 |
| $I_{DSS}$                       | Drain-to-Source Leakage Current      | —    | —     | 25   | μA    | $V_{DS} = 60V, V_{GS} = 0V$                                                 |
|                                 |                                      | —    | —     | 250  |       | $V_{DS} = 48V, V_{GS} = 0V, T_J = 150^\circ\text{C}$                        |
| $I_{GSS}$                       | Gate-to-Source Forward Leakage       | —    | —     | 100  | nA    | $V_{GS} = 20V$                                                              |
|                                 | Gate-to-Source Reverse Leakage       | —    | —     | -100 |       | $V_{GS} = -20V$                                                             |
| $Q_g$                           | Total Gate Charge                    | —    | —     | 67   | nC    | $I_D = 51A$                                                                 |
| $Q_{gs}$                        | Gate-to-Source Charge                | —    | —     | 18   |       | $V_{DS} = 48V$                                                              |
| $Q_{gd}$                        | Gate-to-Drain ("Miller") Charge      | —    | —     | 25   |       | $V_{GS} = 10V$ , See Fig. 6 and 13 ④                                        |
| $t_{d(on)}$                     | Turn-On Delay Time                   | —    | 13    | —    | ns    | $V_{DD} = 30V$                                                              |
| $t_r$                           | Rise Time                            | —    | 97    | —    |       | $I_D = 51A$                                                                 |
| $t_{d(off)}$                    | Turn-Off Delay Time                  | —    | 40    | —    |       | $R_G = 9.1\Omega$                                                           |
| $t_f$                           | Fall Time                            | —    | 57    | —    |       | $R_D = 0.6\Omega$ , See Fig. 10 ④                                           |
| $L_D$                           | Internal Drain Inductance            | —    | 4.5   | —    | nH    | Between lead,<br>6mm (0.25in.)<br>from package<br>and center of die contact |
| $L_S$                           | Internal Source Inductance           | —    | 7.5   | —    |       |                                                                             |
| $C_{iss}$                       | Input Capacitance                    | —    | 1812  | —    | pF    | $V_{GS} = 0V$                                                               |
| $C_{oss}$                       | Output Capacitance                   | —    | 393   | —    |       | $V_{DS} = 25V$                                                              |
| $C_{rss}$                       | Reverse Transfer Capacitance         | —    | 103   | —    |       | $f = 1.0MHz$ , See Fig. 5                                                   |



## Source-Drain Ratings and Characteristics

|          | Parameter                                 | Min.                                                                        | Typ. | Max. | Units | Conditions                                                              |
|----------|-------------------------------------------|-----------------------------------------------------------------------------|------|------|-------|-------------------------------------------------------------------------|
| $I_S$    | Continuous Source Current<br>(Body Diode) | —                                                                           | —    | 55   | A     | MOSFET symbol<br>showing the<br>integral reverse<br>p-n junction diode. |
| $I_{SM}$ | Pulsed Source Current<br>(Body Diode)①    | —                                                                           | —    | 220  |       |                                                                         |
| $V_{SD}$ | Diode Forward Voltage                     | —                                                                           | —    | 2.5  | V     | $T_J = 25^\circ\text{C}, I_S = 51A, V_{GS} = 0V$ ④                      |
| $t_{rr}$ | Reverse Recovery Time                     | —                                                                           | 70   | 105  | ns    | $T_J = 25^\circ\text{C}, I_F = 51A$                                     |
| $Q_{rr}$ | Reverse Recovery Charge                   | —                                                                           | 146  | 219  | nC    | $di/dt = 100A/\mu s$ ④                                                  |
| $t_{on}$ | Forward Turn-On Time                      | Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$ ) |      |      |       |                                                                         |

### Notes:

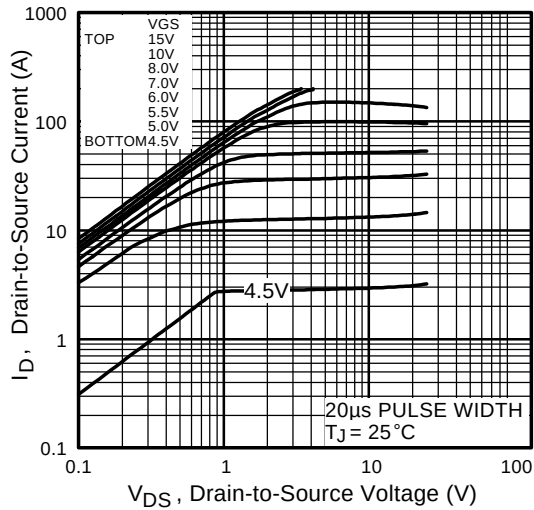
① Repetitive rating; pulse width limited by max. junction temperature. ( See fig. 11 )

② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 89\mu H$   
 $R_G = 25\Omega$ ,  $I_{AS} = 51A$ . (See Figure 12)

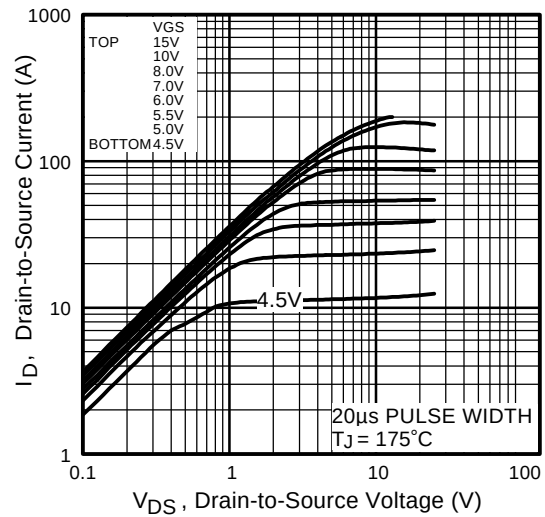
③  $I_{SD} \leq 51A$ ,  $di/dt \leq 227A/\mu s$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  
 $T_J \leq 175^\circ\text{C}$

④ Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$ .

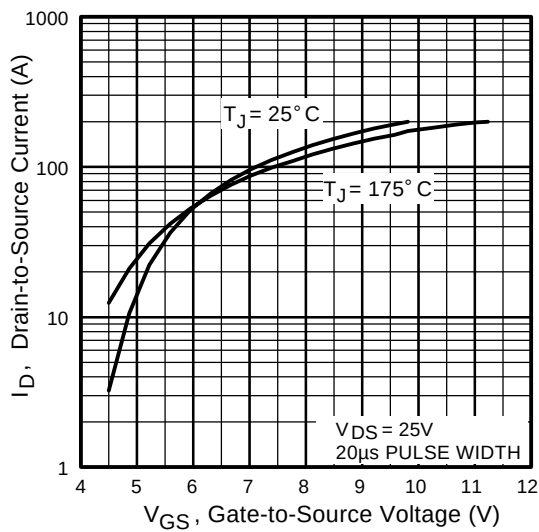
# IRFZ44VS/IRFZ44VL



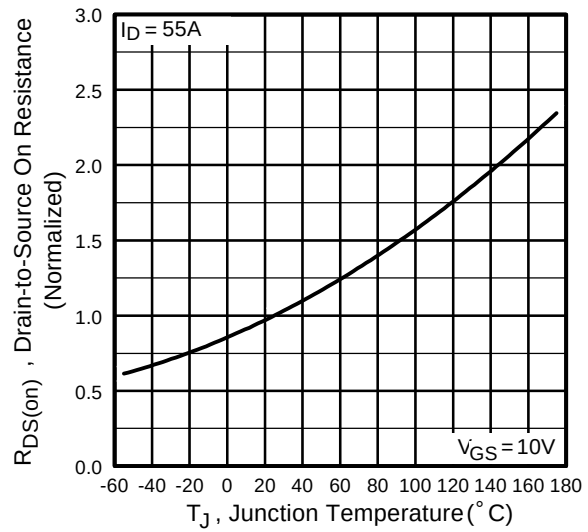
**Fig 1.** Typical Output Characteristics



**Fig 2.** Typical Output Characteristics



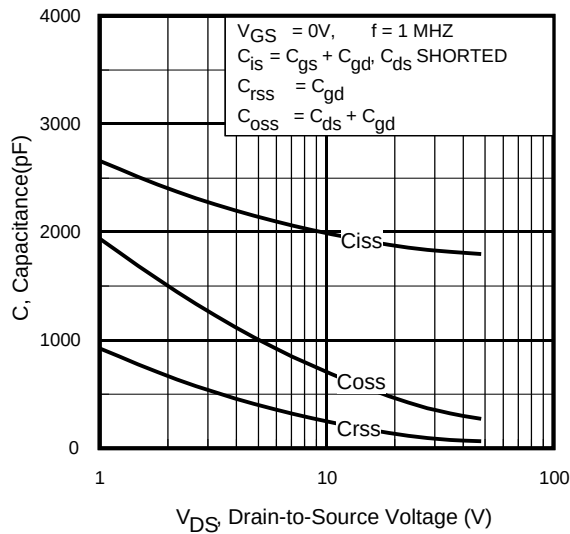
**Fig 3.** Typical Transfer Characteristics



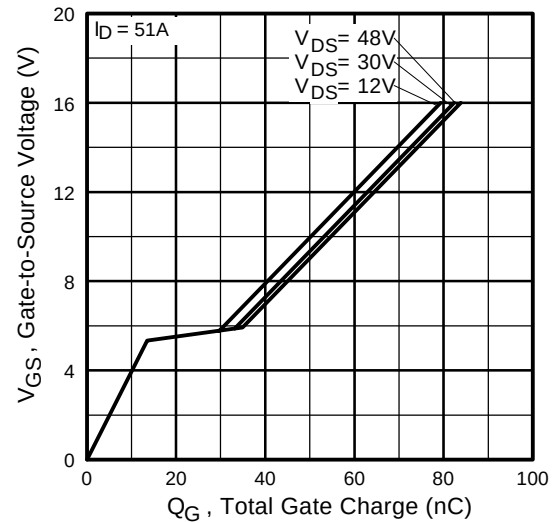
**Fig 4.** Normalized On-Resistance vs. Temperature

# IRFZ44VS/IRFZ44VL

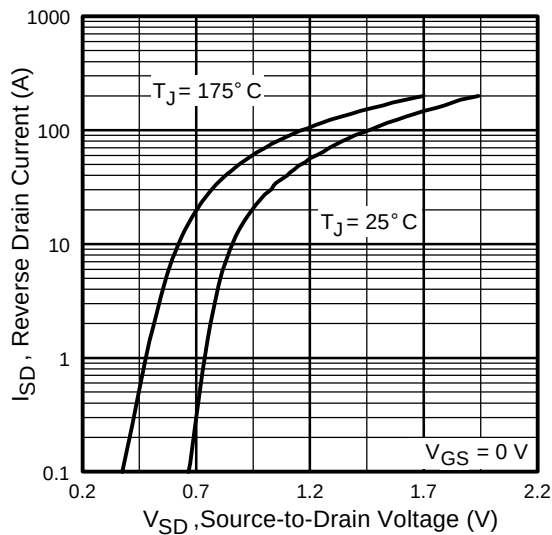
International  
**IR** Rectifier



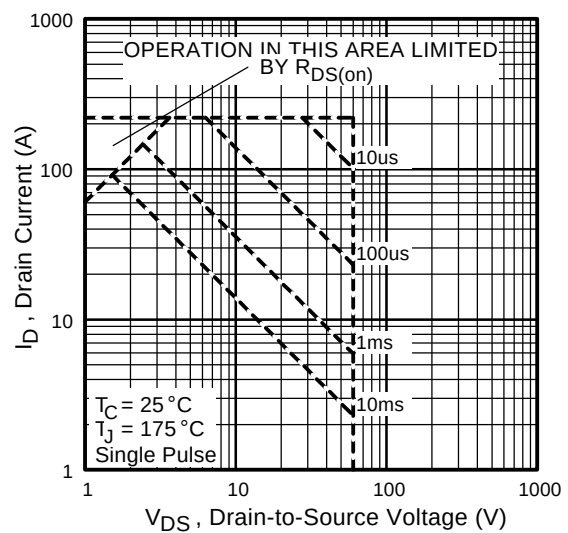
**Fig 5.** Typical Capacitance vs. Drain-to-Source Voltage



**Fig 6.** Typical Gate Charge vs. Gate-to-Source Voltage

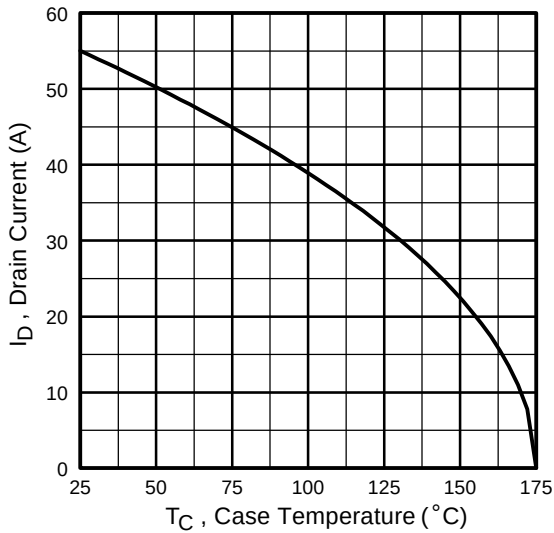


**Fig 7.** Typical Source-Drain Diode Forward Voltage

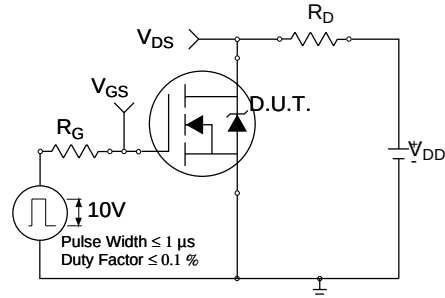


**Fig 8.** Maximum Safe Operating Area

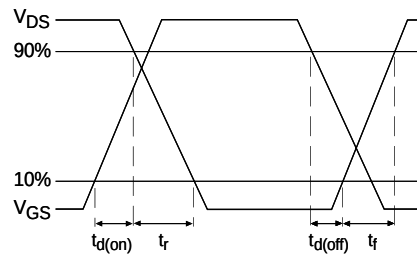
# IRFZ44VS/IRFZ44VL



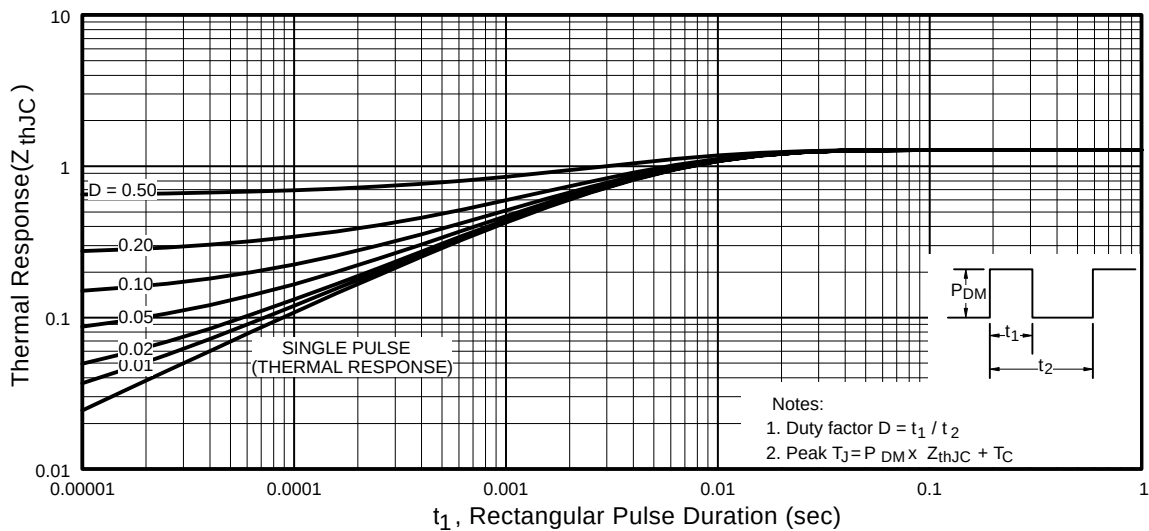
**Fig 9.** Maximum Drain Current vs. Case Temperature



**Fig 10a.** Switching Time Test Circuit



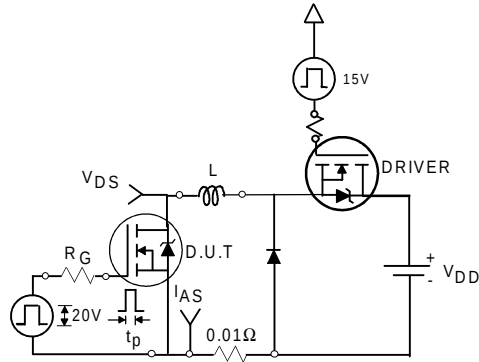
**Fig 10b.** Switching Time Waveforms



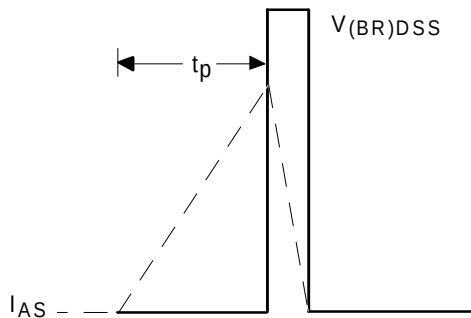
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case

# IRFZ44VS/IRFZ44VL

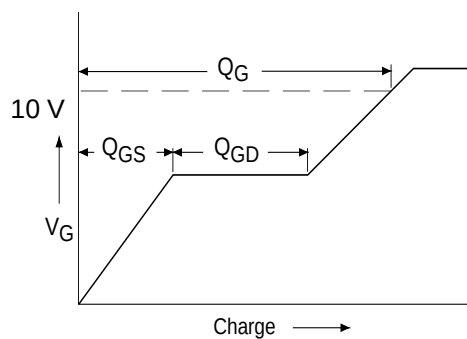
International  
**IR** Rectifier



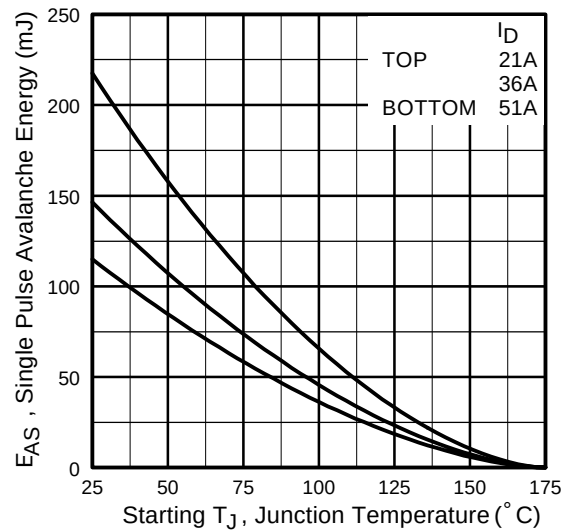
**Fig 12a.** Unclamped Inductive Test Circuit



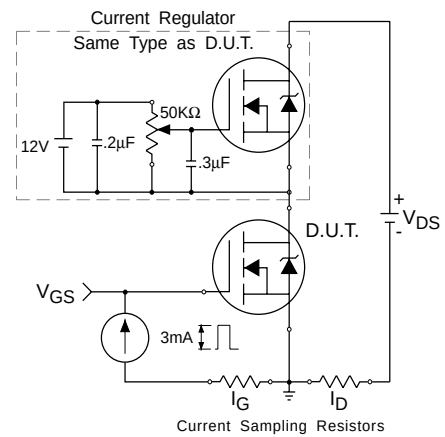
**Fig 12b.** Unclamped Inductive Waveforms



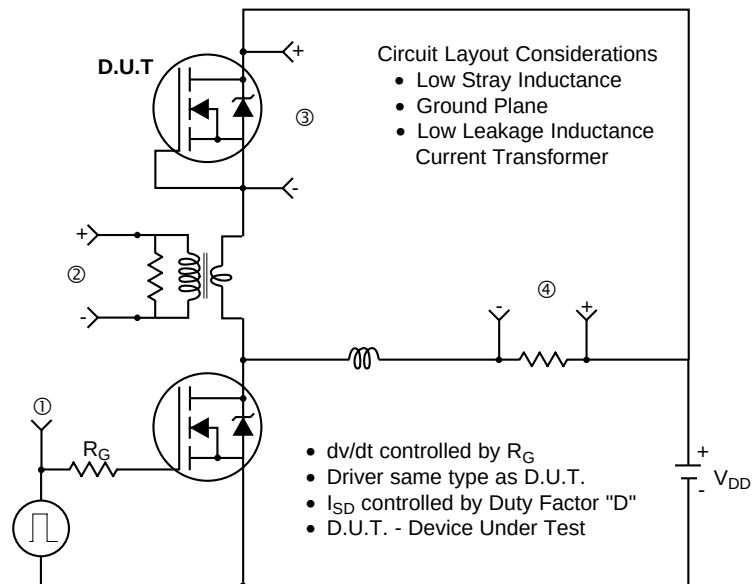
**Fig 13a.** Basic Gate Charge Waveform



**Fig 12c.** Maximum Avalanche Energy vs. Drain Current



**Fig 13b.** Gate Charge Test Circuit

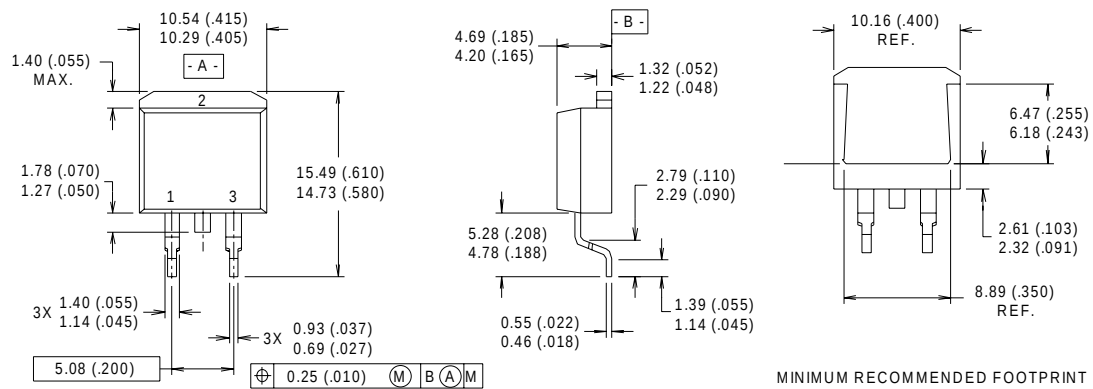


# IRFZ44VS/IRFZ44VL

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## D<sup>2</sup>Pak Package Outline

Dimensions are shown in millimeters (inches)



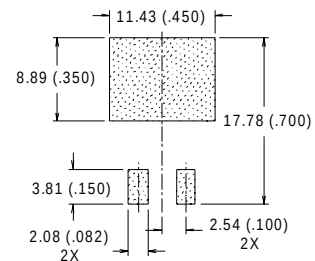
### NOTES:

- 1 DIMENSIONS AFTER SOLDER DIP.
- 2 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
- 3 CONTROLLING DIMENSION : INCH.
- 4 HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

### LEAD ASSIGNMENTS

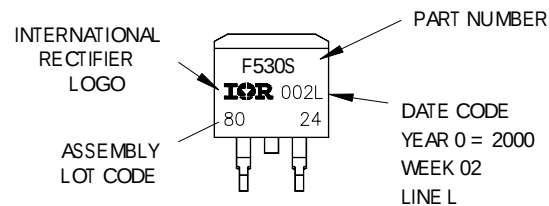
- 1 - GATE
- 2 - DRAIN
- 3 - SOURCE

### MINIMUM RECOMMENDED FOOTPRINT



## D<sup>2</sup>Pak Part Marking Information

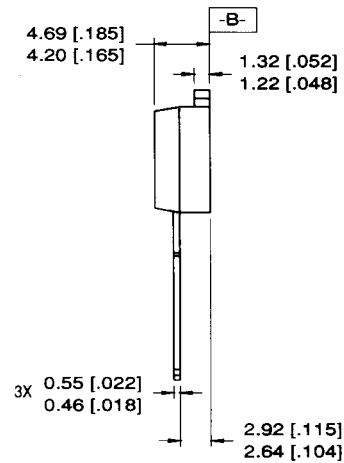
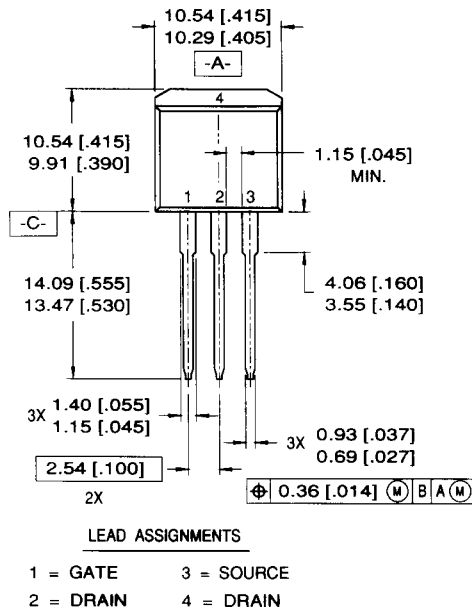
EXAMPLE: THIS IS AN IRF530S WITH  
LOT CODE 8024  
ASSEMBLED ON WW02, 2000  
IN THE ASSEMBLY LINE "L"





## TO-262 Package Outline

Dimensions are shown in millimeters (inches)

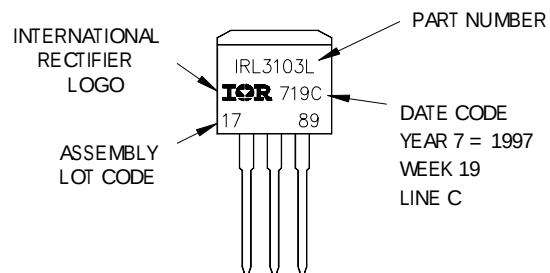


### NOTES:

1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

## TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L  
LOT CODE 1789  
ASSEMBLED ON WW19, 1997  
IN THE ASSEMBLY LINE "C"

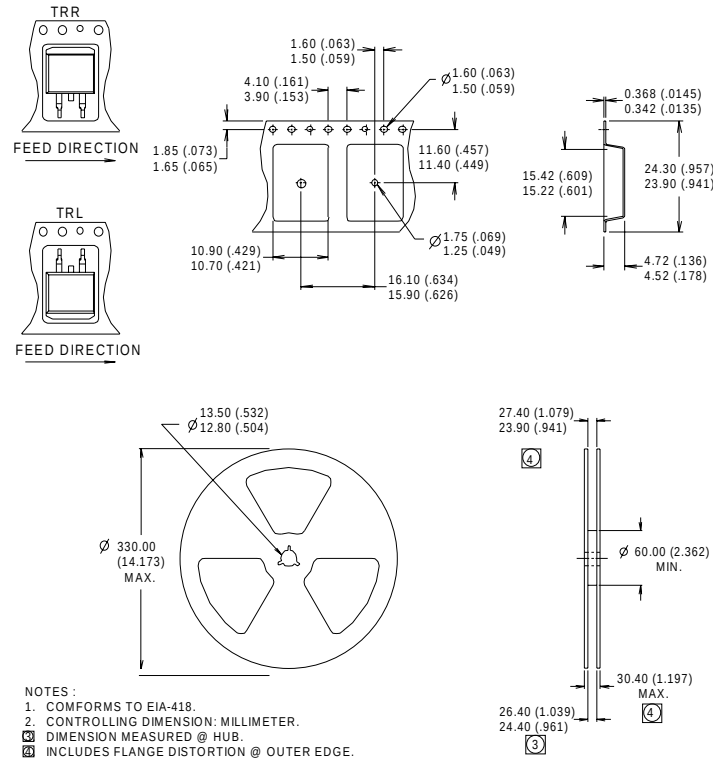


# IRFZ44VS/IRFZ44VL

International  
**IR** Rectifier

## D<sup>2</sup>Pak Tape & Reel Information

Dimensions are shown in millimeters (inches)



Data and specifications subject to change without notice.  
This product has been designed and qualified for the Industrial market.  
Qualification Standards can be found on IR's Web site.

International  
**IR** Rectifier

**IR WORLD HEADQUARTERS:** 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105

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